

REVISION HISTORY

<u>Revision</u>	<u>Description</u>	<u>Issue Date</u>
Rev. 1.0	Initial Issue	July.12. 2012
Rev. 1.1	."CE# $\geq V_{CC} - 0.2V$ " revised as "CE# ≤ 0.2 " for TEST CONDITION of Average Operating Power supply Current Icc1 on page3	July.19. 2012
Rev.1.2	Add "Green package available" on page 1	Nov. 02. 2012
Rev.1.3	1.Revise "TEST CONDITION" for VOH, VOL on page 3 I _{OH} = -8mA revised as -4mA I _{OL} =4mA revised as 8mA 2.Revise VIH(max) & VIL(min) note on page 3 VIH(max) = VCC + 2.0V for pulse width less than 6ns. VIL(min) = VSS - 2.0V for pulse width less than 6ns.	June. 04. 2013
Rev.1.4	Revised the address pin sequence of TSOP-II pin configuration on page 3 in order to be compatible with industry convention. (No function specifications and applications have been changed and all the characteristics are kept all the same as Rev 1.3)	Oct. 30. 2013

FEATURES

- Fast access time : 8/10/12ns
- **Low power consumption:**
 Operating current:
 50/40/35mA(TYP.)
 Standby current:
 2mA(TYP.)
- Single 3.3V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- **Green package available**
- Data retention voltage : 1.5V (MIN.)
- Package : 44-pin 400 mil TSOP-II

GENERAL DESCRIPTION

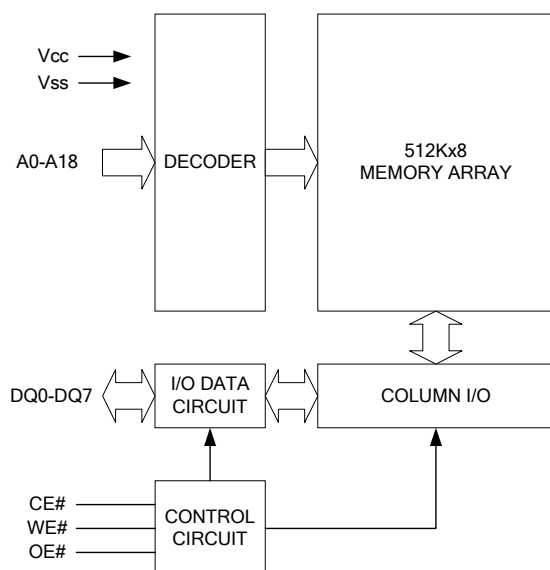
The LY61L5128A is a 4,194,304-bit high speed CMOS static random access memory organized as 524,288 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The LY61L5128A operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation	
				Standby(I _{SB1} ,TYP.)	Operating(I _{CC1} ,TYP.)
LY61L5128A	0 ~ 70°C	2.7 ~ 3.6V	10/12ns	2mA	40/35mA
		3.0 ~ 3.6V	8ns	2mA	50mA
LY61L5128A(I)	-40 ~ 85°C	2.7 ~ 3.6V	10/12ns	2mA	40/35mA
		3.0 ~ 3.6V	8ns	2mA	50mA

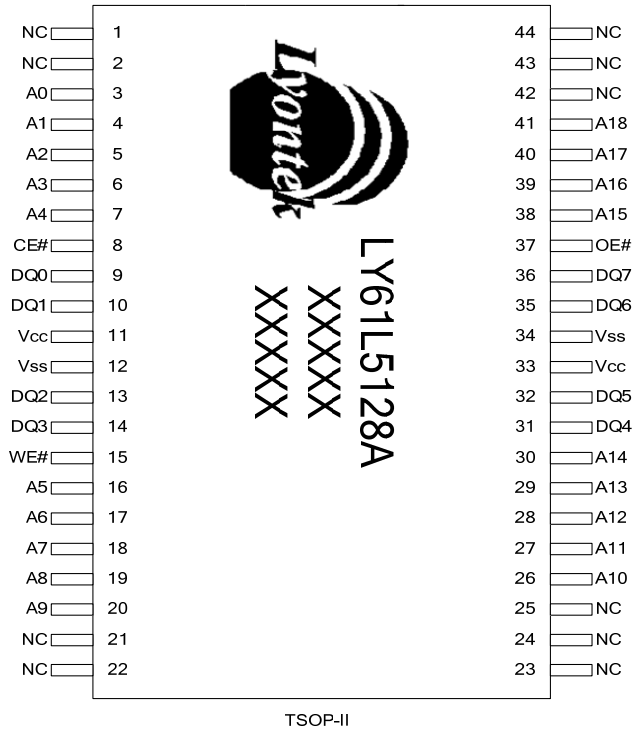
FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A18	Address Inputs
DQ0 - DQ7	Data Inputs/Outputs
CE#	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V _{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to Vss	V _{T2}	-0.5 to V _{CC} +0.5	V
Operating Temperature	T _A	0 to 70(C grade)	°C
		-40 to 85(I grade)	
Storage Temperature	T _{STG}	-65 to 150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High-Z	I _{SB} , I _{SB1}
Output Disable	L	H	H	High-Z	I _{CC} , I _{CC1}
Read	L	L	H	D _{OUT}	I _{CC} , I _{CC1}
Write	L	X	L	D _{IN}	I _{CC} , I _{CC1}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. ⁴	MAX.	UNIT	
Supply Voltage	V _{CC}		-8	3.0	3.3	3.6	V
			-10/-12	2.7	3.3	3.6	V
Input High Voltage	V _{IH} ¹		2.2	-	V _{CC} +0.3	V	
Input Low Voltage	V _{IL} ²		-0.3	-	0.8	V	
Input Leakage Current	I _{LI}	V _{CC} ≥ V _{IN} ≥ V _{SS}	-1	-	1	μA	
Output Leakage Current	I _{LO}	V _{CC} ≥ V _{OUT} ≥ V _{SS} , Output Disabled	-1	-	1	μA	
Output High Voltage	V _{OH}	I _{OH} = -4mA	2.4	-	-	V	
Output Low Voltage	V _{OL}	I _{OL} = 8mA	-	-	0.4	V	
Average Operating Power supply Current	I _{CC}	Cycle time = Min. CE# = V _{IL} , I _{I/O} = 0mA, Others at V _{IL} or V _{IH}	-8	-	65	80	mA
			-10	-	50	70	mA
			-12	-	45	60	mA
Average Operating Power supply Current	I _{CC1}	CE# ≤ 0.2, Others at 0.2V or V _{CC} -0.2V I _{I/O} = 0mA; f = max	-8	-	50	60	mA
			-10	-	40	55	mA
			-12	-	35	50	mA
Standby Power Supply Current	I _{SB}	CE# = V _{IH} , Others at V _{IL} or V _{IH}	-	-	30	mA	
	I _{SB1}	CE# ≥ V _{CC} - 0.2V, Others at 0.2V or V _{CC} - 0.2V	-	2	10	mA	

Notes:

1. V_{IH}(max) = V_{CC} + 2.0V for pulse width less than 6ns.

2. V_{IL}(min) = V_{SS} - 2.0V for pulse width less than 6ns.

3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.

4. Typical values are included for reference only and are not guaranteed or tested.

Typical values are measured at V_{CC} = V_{CC}(TYP.) and T_A = 25°C

CAPACITANCE ($T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	8/10/12ns
Input Pulse Levels	0.2V to $V_{CC} - 0.2V$
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF} + 1\text{TTL}$, $I_{OH}/I_{OL} = -4\text{mA}/8\text{mA}$

AC ELECTRICAL CHARACTERISTICS
(1) READ CYCLE

PARAMETER	SYM.	LY61L5128A-8		LY61L5128A-10		LY61L5128A-12		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	8	-	10	-	12	-	ns
Address Access Time	t_{AA}	-	8	-	10	-	12	ns
Chip Enable Access Time	t_{ACE}	-	8	-	10	-	12	ns
Output Enable Access Time	t_{OE}	-	4.5	-	4.5	-	5	ns
Chip Enable to Output in Low-Z	t_{CLZ}^*	2	-	2	-	3	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	0	-	0	-	0	-	ns
Chip Disable to Output in High-Z	t_{CHZ}^*	-	3	-	4	-	5	ns
Output Disable to Output in High-Z	t_{OHZ}^*	-	3	-	4	-	5	ns
Output Hold from Address Change	t_{OH}	2	-	2	-	2	-	ns

(2) WRITE CYCLE

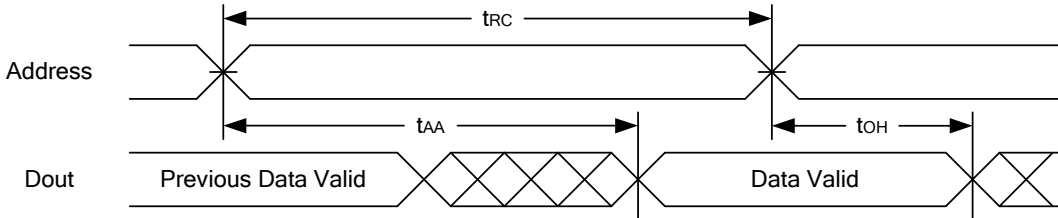
PARAMETER	SYM.	LY61L5128A-8		LY61L5128A-10		LY61L5128A-12		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	8	-	10	-	12	-	ns
Address Valid to End of Write	t_{AW}	6.5	-	8	-	10	-	ns
Chip Enable to End of Write	t_{CW}	6.5	-	8	-	10	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	6.5	-	8	-	10	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	5	-	6	-	7	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	2	-	2	-	2	-	ns
Write to Output in High-Z	t_{WHZ}^*	-	3	-	4	-	5	ns

*These parameters are guaranteed by device characterization, but not production tested.

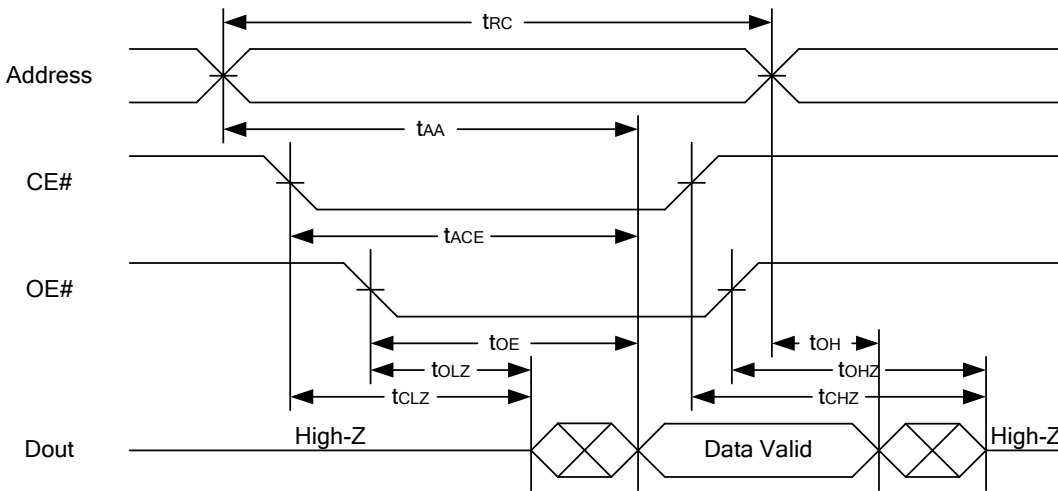


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



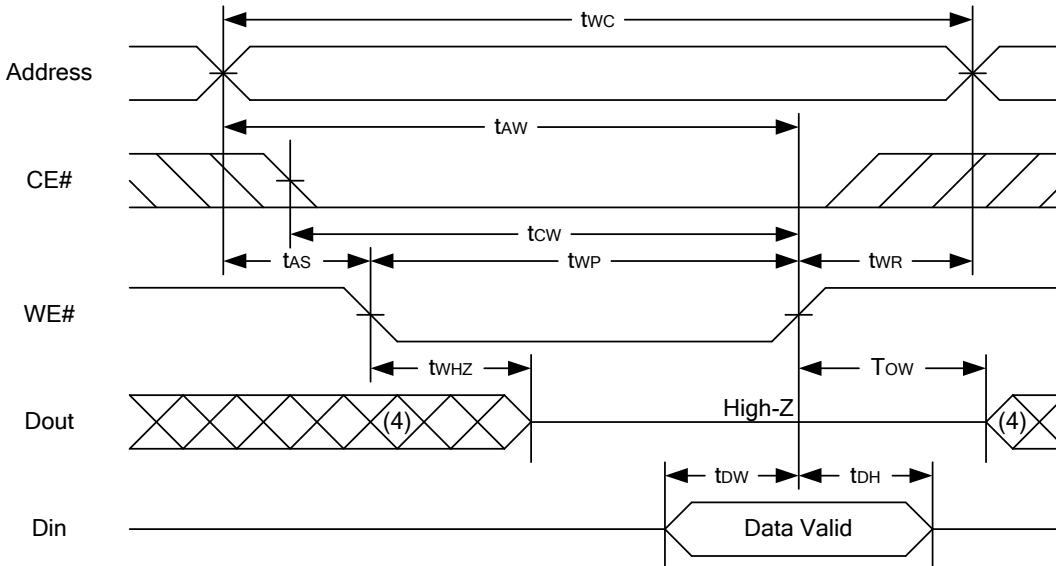
READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



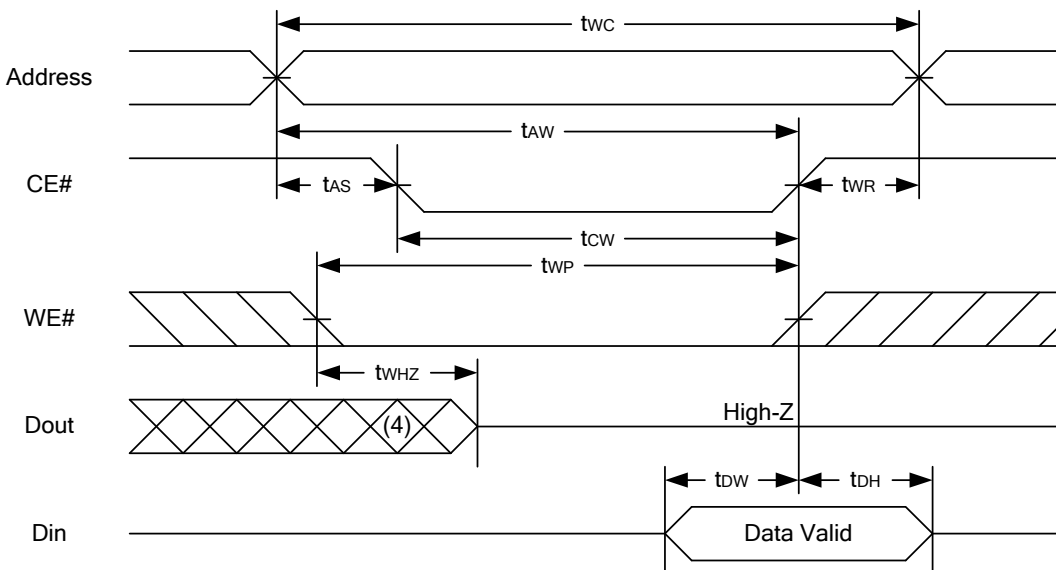
Notes :

1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low.
3. Address must be valid prior to or coincident with CE# = low,; otherwise tAA is the limiting parameter.
4. tCLZ, tOLZ, tCHZ and tOHZ are specified with CL = 5pF. Transition is measured ±500mV from steady state.
5. At any given temperature and voltage condition, tCHZ is less than tCLZ , tOHZ is less than tOLZ.

WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



Notes :

1. WE#, CE# must be high during all address transitions.
2. A write occurs during the overlap of a low CE#, low WE#.
3. During a WE# controlled write cycle with OE# low, tWP must be greater than tWHZ + tDW to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the CE# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
6. tOW and tWHZ are specified with CL = 5pF. Transition is measured ±500mV from steady state.

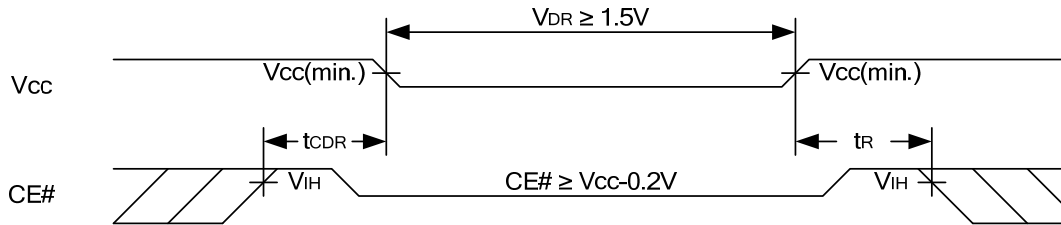


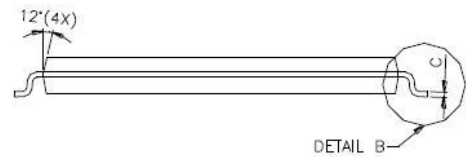
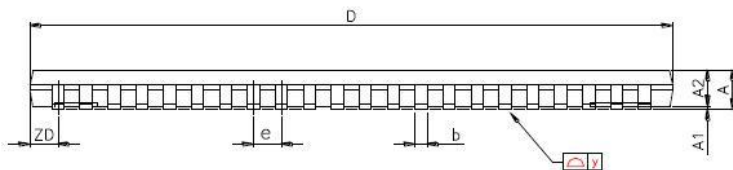
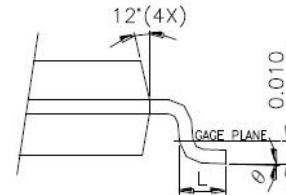
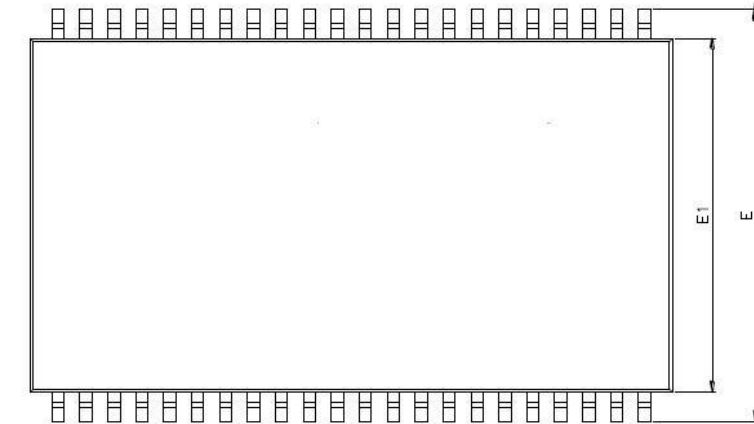
DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	CE# ≥ V _{CC} - 0.2V	1.5	-	3.6	V
Data Retention Current	I _{DR}	V _{CC} = 1.5V CE# ≥ V _{CC} - 0.2V Others at 0.2V or V _{CC} - 0.2V	-	2	10	mA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC*}	-	-	ns

t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM



PACKAGE OUTLINE DIMENSION
44-pin 400mil TSOP-II Package Outline Dimension


SYMBOLS	DIMENSIONS IN MILLMETERS			DIMENSIONS IN MILS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
c	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
e	-	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	-	0.805	-	-	31.7	-
y	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°



ORDERING INFORMATION

Package Type	Access Time (Speed)(ns)	Temperature Range(°C)	Packing Type	Lyontek Item No.
44Pin(400mil) TSOP-II	8	0°C~70°C	Tray	LY61L5128AML-8
			Tape Reel	LY61L5128AML-8T
		-40°C~85°C	Tray	LY61L5128AML-8I
			Tape Reel	LY61L5128AML-8IT
	10	0°C~70°C	Tray	LY61L5128AML-10
			Tape Reel	LY61L5128AML-10T
		-40°C~85°C	Tray	LY61L5128AML-10I
			Tape Reel	LY61L5128AML-10IT



Lyontek Inc.

LY61L5128A

Rev. 1.4

512K X 8 BIT HIGH SPEED CMOS SRAM

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